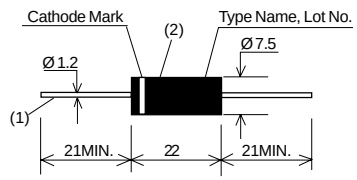
ESJC33-06 (6.4kV/350mA)

HIGH VOLTEGE DIODE

ESJC33 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

Outline Drawings



Unit : mm

No.	Part name	Material and type name
1	Lead wire	Ag plated Cu wire
2	Molding resin	Epoxy resin ULV-0

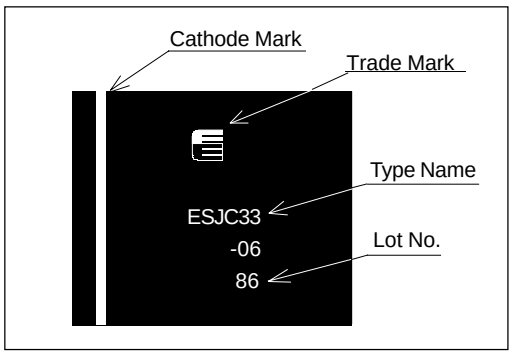
Features

- Low V_F
- High surge proof resistivity
- High reliability .
- High speed switching

Applications

- Rectification for inverter type Microwave oven high voltage power supply

Cathode Mark,Type Name



Maximum Ratings and Characteristics

- Absolute Maximum Ratings

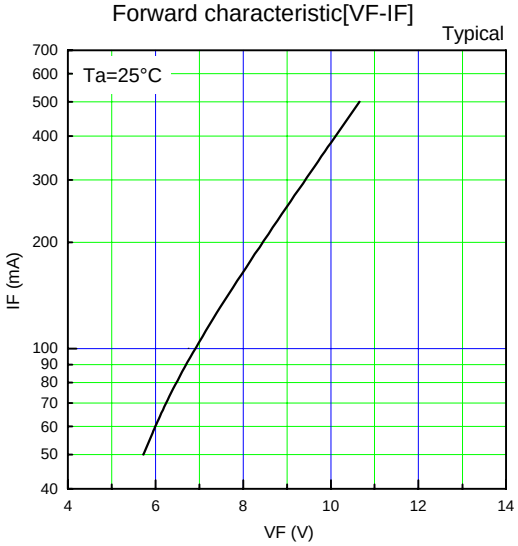
Items	Symbols	Conditions	ESJC33-06	Units
Repetitive Peak Reverse Voltage	V_{RRM}		6.4	kV
Average Forward Current	Io	Tl ≦ 110°C	350	mA
Non-repetitive Peak Forward Current	I_{FSM}	50Hz.sine harf-wave peak value. One-shot.Ta=25°C	15	A
Non-repetitive Peak Reverse Current	I_{RSM}	Tw=1mS. Rectangular-wave. One-shot.Ta=25°C	50	mA
Allowable Junction Temperature	T_j		120	°C
Storage Temperature Range	Tstg		-30 to +130	°C

- Electrical Characteristics (Ta=25°C Unless otherwise specified)

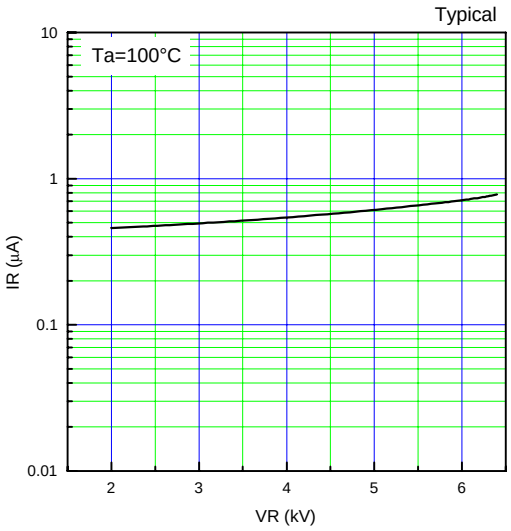
Items	Symbols	Conditions	ESJC33-06	Units
Maximum Forward Voltage Drop	V_F	I_F=350mA	12	V
Maximum Reverse Current	I_R	V_R=6.4kV	10	μA
Minimum Reverse Recovery Time	trr	IF=100mA, IR=100mA 90%Recovery	0.15	μs

■ Characteristics

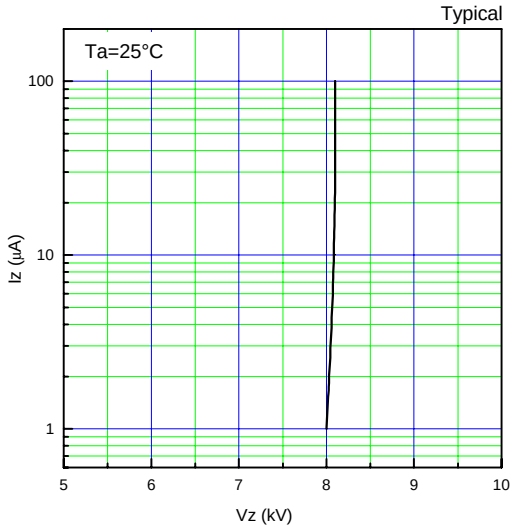
Forward characteristic[VF-IF]



Reverse characteristic[VR-IR]



Avalanche characteristic[Vz-Iz]



Reverse recovery time characteristic[Ta-trr]